



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Hideomi Suzawa et al.
 Serial No. : 09/852,672
 Filed : May 11, 2001
 Title : SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

Commissioner for Patents
 Washington, D.C. 20231

Art Unit : 2812
 Examiner : Viktor Simkovic
 Confirmation No. 5083

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RESPONSE TO OFFICE ACTION

In response to the action mailed June 19, 2002, please amend the application as follows:

In the claims:

Please cancel claims 1-8 without prejudice or disclaimer.

Please amend claims 28 and 33 as follows:

-- 28. (Amended) A method of manufacturing a semiconductor device comprising steps of:

- forming a semiconductor layer on an insulating surface;
- forming an insulating film on said semiconductor layer;
- laminating a first conductive film and a second conductive film on said insulating film;

- forming a second conductive layer with a first width;
- adding an impurity element to said semiconductor layer using said second conductive layer with said first width as a mask to form a high concentration impurity region;

- etching said first conductive film to form a first electrode comprising a laminate structure of a first conductive layer with a second width and said second conductive layer with a third width;

- etching said second conductive layer to form a second electrode comprising a laminate structure of said first conductive layer with said second width and said second conductive layer with a fourth width;